

140 COMMERCE DRIVE MONTGOMERYVILLE, PA 18936-1013

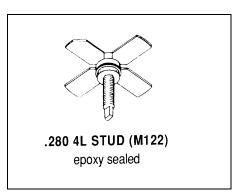
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MS1426

RF & MICROWAVE TRANSISTORS UHF MOBILE APPLICATIONS

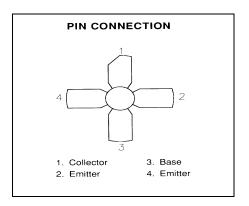
Features

- 470 MHz
- 12.5 VOLTS
- P_{OUT} = 10 WATTS
- $G_P = 8.0 \text{ dB MINIMUM}$
- COMMON EMITTER CONFIRGURATION



DESCRIPTION:

The MS1426 is a epitaxial silicon NPN planar transistor designed for Class C driver applications in the 450 - 512 MHz frequency range. This device uses an emitter ballasted die geometry specifically designed for optimum stable power gain, maximum efficiency and infinite VSWR capability.



ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit
$V_{\sf CBO}$	Collector-Base Voltage	36	V
V _{CEO}	Collector-Emitter Voltage	16	V
V _{CES}	Collector-Emitter Voltage	36	V
V _{EBO}	Emitter-Base Voltage	4.0	V
Ic	Device Current	2.5	Α
P _{DISS}	Power Dissipation	58	W
T J	Junction Temperature	200	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Thermal Data

R _{TH(J-C)} Junction-case Thermal Resistance	3.0	°C/W
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ELECTRICAL SPECIFICATIONS (Tcase = 25°C) STATIC

Symbol	Test Conditions		Value			
		Min.	Typ.	Max.	Unit	
BV _{CES}	I _C = 25 mA	V _{BE} = 0 V	36			V
BV _{CEO}	I _C = 20 mA	I _B = 0 mA	16			V
BV _{EBO}	I _E = 10 mA	I _C = 0 mA	4.0			V
I _{CES}	V _{CE} = 10 V	I _E = 0 mA			3.0	mA
I _{CBO}	V _{CB} = 15V	I _E = 0 mA			2.0	mA
H _{FE}	V _{CE} = 5 V	I _C = 1 A	10		150	

DYNAMIC

Symbol	Test Conditions		Value		Unit		
Syllibol			Min.	Тур.	Max.	Offic	
P _{out}	f = 470 MHz	$P_{IN} = 2.0W$	$V_{CE} = 12.5V$	10			w
G _P	f = 470 MHz	P _{IN} = 2.0W	V _{CE} = 12.5V	7			dB
Сов	f = 1 MHz	$V_{CB} = 12.5V$				26	pf

IMPEDANCE DATA

FREQ	$Z_IN(\Omega)$	$Z_{\mathtt{CL}}(\Omega)$		
470MHz	1.5 - j2.7	5.7 + j1.5		

 $P_{IN} = 2.0W$ $V_{CE} = 12.5V$





PACKAGE MECHANICAL DATA

